

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
		"6002523"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/18 08:23
		2003/0024905 2003/0059990 "6", "160,827" "5,953,597" "6,204,099" "5,712,191" "5,937,282" "6,242,289" "4,330,363" "5,854,803" "6,210,996" "6,265,745"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/18 07:52
		S33 and ((incident reflect\$3) near S25 beam)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/17 13:51
L1	2	2003/0024905	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/18 08:01
L2	0	2003/0059990	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/18 08:02
L3	1	"20030059990"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/18 08:02
L4	13	"6160827"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/18 08:04
L5	13	"6160827"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/18 08:17
L6	1	"6556711"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/18 08:17
L7	27	"6013928"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/18 08:23

L8	8	"6008523"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/18 08:24
L9	6	"6310727"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/18 08:26
L10	1	"6512634"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/18 08:34
L11	1	10/021719	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/18 08:34
S22	71408	(wafer substrate) with laser	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/17 13:06
S23	38234	S22 and laser near3 beam	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/17 13:07
S24	16417	S23 and (irradiat\$4 irradiation irradiat\$2)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/17 13:08
S25	6996	S24 and ((irradiat\$4 irradiation irradiat\$2) with surface)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/17 13:08
S26	2180	S25 and ((irradiat\$4 irradiation irradiat\$2) with (target source))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/17 13:53
S27	834	S26 and ((irradiat\$4 irradiation irradiat\$2) with semiconductor)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/17 13:10
S28	223	S27 and ((irradiat\$4 irradiation irradiat\$2) with angle)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/17 13:55

S29	58	S28 and ((tilt\$2 oblique\$3) with angle)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/17 13:52
S30	23	S29 and (laser near3 anneal\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/17 13:46
S31	1	10/021719	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/17 13:14
S32	1329	((semiconductor silicon amorphous) with (substrate wafer)) with (laser near3 anneal\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/17 13:48
S33	1329	S32 and (laser beam)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/17 13:49
S34	320	S33 and ((incident reflect\$3) near4 beam)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/17 14:10
S35	237	S34 and (tilt\$2 oblique\$3 angle)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/17 14:11
S36	83	S35 and ((irradit\$4 irradiation irradiat\$2) with (target source))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/17 13:53
S37	83	S36 and ((irradit\$4 irradiation irradiat\$2) with (area surface))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/17 14:11
S38	46	S37 and ((irradit\$4 irradiation irradiat\$2) with angle)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/17 13:55
S39	326	S33 and ((incident incidence reflect\$3) near4 beam)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/17 14:10

S40	242	S39 and (tilt\$2 oblique\$3 angle)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/17 14:11
S41	190	S40 and ((irradit\$4 irradiation irradiat\$2) with (area surface))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/03/18 07:51